

PE565211

Document Category: Product Concept

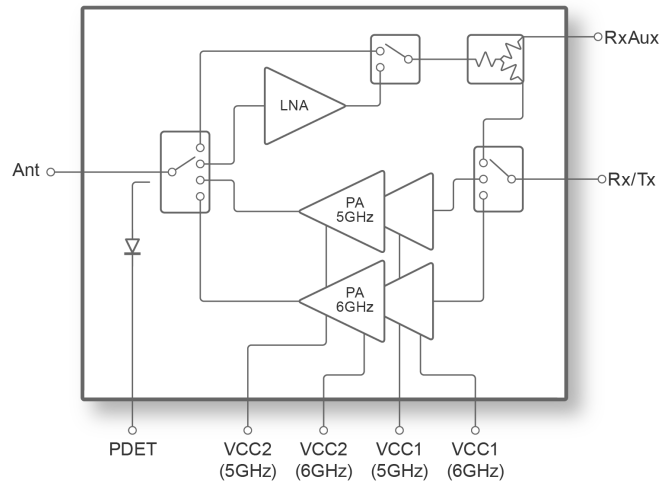
5–7 GHz 802.11ax SOI Wi-Fi Front-End Module



Features

- Single-die 5–7 GHz, PA, LNA, bypass path with RxAux port
- Fully-matched input and output
- Integrated logarithmic power detector
- Tx Gain: 5 GHz: 27 dB, 6 GHz: 21 dB typical
- Rx Gain: 5 GHz: 15 dB, 6 GHz: 13 dB typical
- Rx NF: 5 GHz: 2.1 dB, 6 GHz: 2.3 dB typical
- Excellent long packet EVM performance:
 - MCS11 5 GHz: -41 dB @ 12.5 dBm (HE80)
 - MCS11 6 GHz: -41 dB @ 13.0 dBm (HE80)
- Packaging — Ultra-compact 16-lead 2.5 x 2.5 mm LGA (MSL3)

Figure 1 ■ PE565211 Functional Diagram



Applications

- Nominal- to medium-power 802.11ax CPE (routers, extenders, access points and gateways)
- PC cards, PCMCIA cards, mini and half-mini cards
- Wi-Fi-enabled video systems
- POE
- IoT

Product Description

The PE565211 is a high-performance, fully integrated 5–7 GHz 802.11ax Wi-Fi front-end module (FEM) that combines the intelligent integration capabilities of pSemi's patented UltraCMOS® technology. The device provides all the functionality of a fully-matched bypassable amplifier (LNA), a dual-core power amplifier (PA) and two RF switches (SP4T, SP3T). The all-silicon die enables an ultra-compact industry-leading 2.5 x 2.5 mm 16-lead LGA package to minimize valuable PCB layout area, especially for high-density MIMO applications.

The PE565211 maintains maximum linear PA output power from a 3.85V supply for optimal power savings while low LNA NF enhances receive sensitivity and improves range over a wide variety of conditions. The PE565211 also includes an integrated logarithmic power detector and die-level filtering for sub-harmonic 2.4 GHz rejection for DBDC operation.

The PE565211 is manufactured on pSemi's UltraCMOS process, a patented advanced form of silicon-on-insulator (SOI) technology, offering the performance of GaAs with the economy and integration of conventional CMOS.

Recommended Operating Conditions

Table 1 lists the recommending operating conditions for the PE565211. Devices should not be operated outside the operating conditions listed below.

Table 1 ■ Recommended Operating Conditions for PE565211

Parameter	Condition	Min	Typ	Max	Unit
Operating Voltage		3.0	3.85	5.0	V
Sleep Current				20	μA
Switching Time (LNA)			200	400	ns
Switching Time (PA)			200	400	ns
Control Logic High		1.08	1.8	1.98	V
Control Logic Low			0.2	0.45	V
Operating temperature		-40	25	+85	C

Electrical Specifications

Table 2 provides the PE565211 key electrical specifications @ 3.85V, +25 °C, unless otherwise specified.

Table 2 ▪ PE565211 Electrical Specifications

Parameter	Condition	Min	Typ	Max	Unit
Tx Low-band (5–6 GHz)					
Frequency Range		5150		5950	MHz
PA Gain	At EVM POUT		27		dB
PA Gain Variation	Over 160 MHz channel		0.1		dB
Out-of-Band Gain	3660-3900 MHz, small signal		19		dB
	4400-5000 MHz, small signal		27		dB
Out-of-Band Noise Density	+/- 170 MHz offset		-116		dBm/ Hz
	+/- 290 MHz offset		-116		dBm/ Hz
80 MHz 1024Q Linear Power (EVM)	EVM <-30 dB		21		dB
	EVM <-35 dB		17		dB
	EVM <-38 dB		15		dB
	EVM <-41 dB		12.5		dB
	EVM <-50 dB		PASS		dB
160 MHz 1024Q Linear Power (EVM)	EVM <-30 dB		21		dB
	EVM <-35 dB		16		dB
	EVM <-38 dB		13.5		dB
	EVM <-41 dB		11		dB
	EVM <-50 dB		PASS		dB
Harmonic	All harmonics with all rates, BWs at POUT = 20 dBm		-37		dBm/ MHz
Spectral Mask Margin (MCS0)	Standard w/ 3dB margin @ POUT=21dBm		3.3		dB
Current Consumption	POUT=21 dBm		251		mA
	POUT=19 dBm		220		mA
	POUT=17.5 dBm		205		mA
	POUT=16.5 dBm		196		mA
	POUT=15.5 dBm		190		mA
	POUT=14.5 dBm		185		mA
Tx High-band (6–7 GHz)					
Frequency Range		5900		7150	MHz

Table 2 ▪ PE565211 Electrical Specifications (Cont.)

Parameter	Condition	Min	Typ	Max	Unit
PA Gain	At EVM POUT		21.5		dB
PA Gain Variation	Over 160 MHz channel		0.2		dB
Out-of-Band Gain	3660-3900 MHz, small signal		-3		dB
	4400-5000 MHz, small signal		17		dB
Out-of-Band Noise Density	+/- 170 MHz offset		-116		dBm/Hz
	+/- 290 MHz offset		-115		dBm/Hz
80 MHz 1024Q Linear Power (EVM)	EVM <-30 dB		21		dB
	EVM <-35 dB		16.5		dB
	EVM <-38 dB		15		dB
	EVM <-41 dB		13		dB
	EVM <-50 dB		PASS		dB
160 MHz 1024Q Linear Power (EVM)	EVM <-30 dB		21		dB
	EVM <-35 dB		15		dB
	EVM <-38 dB		13.5		dB
	EVM <-41 dB		12		dB
	EVM <-50 dB		PASS		dB
Harmonic	All harmonics with all rates, BWs at POUT = 20 dBm		N/A		dBm/MHz
Spectral Mask Margin (MCS0)	Standard w/ 3 dB margin @ POUT=21 dBm		2.7		dB
Current Consumption	POUT=21 dBm		280		mA
	POUT=19 dBm		220		mA
	POUT=17.5 dBm		205		mA
	POUT=16.5 dBm		210		mA
	POUT=15.5 dBm		200		mA
	POUT=14.5 dBm		190		mA
Tx Low/High-band PDET (5-7GHz)					
Detector Range		-10		21	dBm
Detector Output	noRF-21 dBm (measured at the peak of preamble of OFDM packet)	250		1250	mV
Tx Low-band, 5G PDET					
Linear Detector @ 0 dBm			370		mV
Linear Detector @ 21 dBm			1030		mV

Table 2 ■ PE565211 Electrical Specifications (Cont.)

Parameter	Condition	Min	Typ	Max	Unit
Tx High-band, 6G PDET					
Linear Detector @ 0 dBm			350		mV
Linear Detector @ 21 dBm			1000		mV
Power Detector Output Impedance				5	kΩ
Power Detector Output Impedance		5			MΩ
Detector BW		1		3	MHz
Rx Low-band (5–6 GHz)					
Frequency Range		5150		5950	MHz
Rx Aux to Tx/Rx Isolation	All Rx and RxAux modes		10		dB
High Gain Mode					
Gain			14		dB
Gain	At 2400-2500 MHz (Out-of-band gain)		-34		dB
Gain variation	Over 160 MHz channel		0.2		
Noise Figure			2.1		dB
Input Return Loss			4		dB
Output Return Loss			4		dB
Input IP3			-7		dBm
Input P1dB			-10		dBm
LNA Bias Current			11		mA
Bypass Mode					
Gain			-5.9		dB
Input Return Loss			8		dB
Output Return Loss			7		dB
Input IP3			45		dBm
Input P1dB			31		dBm
Current			19		μA
RxAux Low-band (5–6 GHz)					
Frequency Range		5150		5950	MHz
Rx Aux to Tx/Rx Isolation	All Rx and RxAux modes		10		dB

Table 2 ▪ PE565211 Electrical Specifications (Cont.)

Parameter	Condition	Min	Typ	Max	Unit
High Gain Mode					
Gain			15		dB
Gain	At 2400-2500 MHz (Out-of-band gain)		-34		dB
Gain Variation	Over 160 MHz channel		0.2		
Noise Figure			2.1		dB
Input Return Loss			4		dB
Output Return Loss			5		dB
Input IP3			-7		dBm
Input P1dB			-10		dBm
Saturation Power					dBm
LNA Bias Current			11		mA
Bypass Mode					
Gain			-5.5		dB
Input Return Loss			8		dB
Output Return Loss			10		dB
Input IP3			45		dBm
Input P1dB			31		dBm
Current			19		μA
Rx High-band (6–7 GHz)					
Frequency Range		5900		7150	MHz
Rx Aux to Tx/Rx Isolation	All Rx and RxAux modes		13		dB
High Gain Mode					
Gain			13		dB
Gain	At 2400-2500 MHz (Out-of-band gain)		-34		dB
Gain Variation	Over 160 MHz channel		0.2		
Noise Figure			2.1		dB
Input Return Loss			10		dB
Output Return Loss			6		dB
Input IP3			-7		dBm
Input P1dB			-15		dBm

Table 2 ■ PE565211 Electrical Specifications (Cont.)

Parameter	Condition	Min	Typ	Max	Unit
Saturation Power			TBD		dBm
LNA Bias Current			11		mA
Bypass Mode					
Gain			-7		dB
Input Return Loss			8		dB
Output Return Loss			10		dB
Input IP3			45		dBm
Input P1dB			31		dBm
Current			19		μA
RxAux High-band (6–7 GHz)					
Frequency Range		5900		7150	MHz
Rx Aux to Tx/Rx Isolation	All Rx and RxAux modes		13		dB
High Gain Mode					
Gain			13		dB
Gain	At 2400–2500 MHz (Out-of-band gain)		-34		dB
Gain Variation	Over 160 MHz channel		0.2		
Noise Figure			2.1		dB
Input Return Loss			10		dB
Output Return Loss			12		dB
Input IP3			-7		dBm
Input P1dB			-15		dBm
LNA Bias Current			11		mA
Bypass Mode					
Gain			-5.5		dB
Input Return Loss			10		dB
Output Return Loss			15		dB
Input IP3			45		dBm
Input P1dB			31		dBm
Current			19		μA

Truth Table

Table 3 provides the control logic truth table for the PE565211.

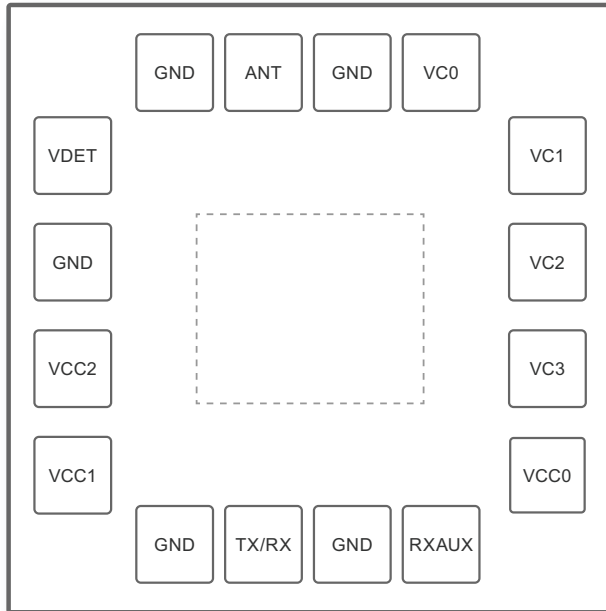
Table 3 ▪ Truth Table for PE565211

Operating Mode	VC0	VC1	VC2	VC3	PATH ANT-TX	PATH ANT-RX	LNA	PA High Band	PA Low Band
TxH	1	0	1	X	ON	OFF	OFF	ON	OFF
Rx LNA	1	0	0	X	OFF	ON	ON	OFF	OFF
Rx Bypass	1	1	0	X	OFF	ON	OFF	OFF	OFF
TxL	1	1	1	X	ON	OFF	OFF	OFF	ON
RxAux LNA On	0	0	0	1	OFF	ON	ON	OFF	OFF
RxAux Bypass	0	0	0	0	OFF	ON	OFF	OFF	OFF

Pin Information

This section provides pinout information for the PE565211. **Figure 2** shows the pin map of this 2.5 × 2.5 mm device for the available package.

Figure 2 ▪ *Pin Configuration (Top View)*



Document Category

Product Concept

The product presented is in concept stage. It is not an approved product nor is it guaranteed to ever be produced or offered for sale. This document is not intended to be used as a datasheet or basis for a design. All values and diagrams are simulations only and are subject to change at any time.

Sales Contact

For additional information, contact Sales at sales@psemi.com.

Disclaimers

The information in this datasheet is believed to be reliable. However, pSemi assumes no liability for the use of this information. Use shall be entirely at the user's own risk. No patent rights or licenses to any circuits described in this datasheet are implied or granted to any third party. pSemi's products are not designed or intended for use in devices or systems intended for surgical implant, or in other applications intended to support or sustain life, or in any application in which the failure of the pSemi product could create a situation in which personal injury or death might occur. pSemi assumes no liability for damages, including consequential or incidental damages, arising out of the use of its products in such applications.

Patent Statement

pSemi products are protected under one or more of the following U.S. patents: patents.psemi.com

Copyright and Trademark

©2020, pSemi Corporation. All rights reserved. The Peregrine Semiconductor name, Peregrine Semiconductor logo and UltraCMOS are registered trademarks and the pSemi name, pSemi logo, HaRP and DuNE are trademarks of pSemi Corporation in the U.S. and other countries.